



NPN BDX54 – BDX54A – BDX54B – BDX54C

SILICON POWER DARLINGTON TRANSISTORS

The BDX54, BDX54A, BDX54B and BDX54C are silicon epitaxial-base PNP transistors in monolithic Darlington configuration and are mounted in Jedec TO-220 plastic package. They are intended for use in audio amplifiers, medium power linear and switching applications. The complementary NPN types are the BDX53, BDX53A, BDX53B and BDX53C respectively. Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CEO}	Collector-Emitter Voltage	$I_B=0$	BDX54	-45	V
			BDX54A	-60	
			BDX54B	-80	
			BDX54C	-100	
V_{CBO}	Collector-Base Voltage	$I_E=0$	BDX54	-45	V
			BDX54A	-60	
			BDX54B	-80	
			BDX54C	-100	
V_{EBO}	Emitter-Base Voltage	$I_C=0$	-5	V	
I_C	Collector Current	$I_{C(RMS)}$	-8	A	
		I_{CM}	-12		
I_B	Base Current		-0.2	A	
P_T	Power Dissipation	@ $T_C = 25^\circ$	60	W	
T_J	Junction Temperature		150	°C	
T_S	Storage Temperature		-65 to +150		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	2.08	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$V_{CE(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -100 \text{ mA}$ $I_B = 0$	BDX54	-45	-	-	V
			BDX54A	-60	-	-	
			BDX54B	-80	-	-	
			BDX54C	-100	-	-	
I_{CEO}	Collector Cutoff Current	$V_{CB} = -22 \text{ V}, I_B = 0$ $V_{CB} = -30 \text{ V}, I_B = 0$ $V_{CB} = -40 \text{ V}, I_B = 0$ $V_{CB} = -50 \text{ V}, I_B = 0$	BDX54	-	-	-0.5	mA
			BDX54A	-	-		
			BDX54B	-	-		
			BDX54C	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE} = -5 \text{ V}$	BDX54	-	-	-2	mA
			BDX54A				
			BDX54B				
			BDX54C				
I_{CBO}	Collector-Base Cutoff Current	$V_{CBO} = -45 \text{ V}, I_E = 0$ $V_{CBO} = -60 \text{ V}, I_E = 0$ $V_{CBO} = -80 \text{ V}, I_E = 0$ $V_{CBO} = -100 \text{ V}, I_E = 0$	BDX54	-	-	-0.2	mA
			BDX54A	-	-		
			BDX54B	-	-		
			BDX54C	-	-		
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -3 \text{ A}, I_B = -12 \text{ mA}$	BDX54	-	-	-2	V
			BDX54A				
			BDX54B				
			BDX54C				
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	$I_C = -3 \text{ A}, I_B = -12 \text{ mA}$	BDX54	-	-	-2.5	V
			BDX54A				
			BDX54B				
			BDX54C				
V_F	Forward Voltage (pulse method)	$I_F = -3 \text{ A}$	BDX54	-	-	-4.0	V
			BDX54A				
			BDX54B				
			BDX54C				
		$I_F = -8 \text{ A}$	BDX54	-	-1.8	-2.5	V
			BDX54A	-	-2.5	-	
			BDX54B	-	-2.5	-	
			BDX54C	-	-2.5	-	
h_{FE}	DC Current Gain (*)	$V_{CE} = -3 \text{ V}, I_C = -3 \text{ A}$	BDX54	750	-	-	-
			BDX54A				
			BDX54B				
			BDX54C				

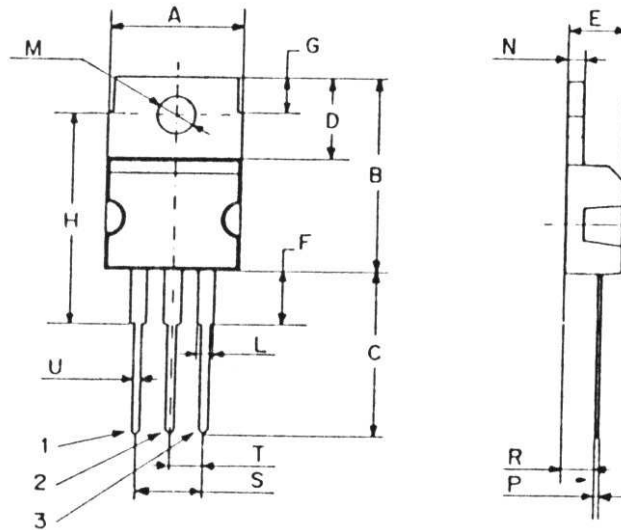
(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 1.5\%$



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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Case :	Collector

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